Silicon PNP Power Transistors 2SB656

DESCRIPTION

·With TO-3 package

·High power dissipation

APPLICATIONS

·For use in power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-160	V
V_{CEO}	Collector-emitter voltage	Open base	-160	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
I_B	Base current		-4	A
P_C	Collector power dissipation	T_C=25□	125	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA ;I_B=0	-160			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA ;I_E=0	-160			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA ;I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-10A; I_B=-1A			-3.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-160V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-0.1	mA
h_{FE}	DC current gain	I_C=-1A ; V_{CE}=-5V	60		200	
f_T	Transition frequency	I_C=-1A ; V_{CE}=-10V		20		MHz

◆ h_{FE} Classifications

B	C
60-120	100-200

PACKAGE OUTLINE

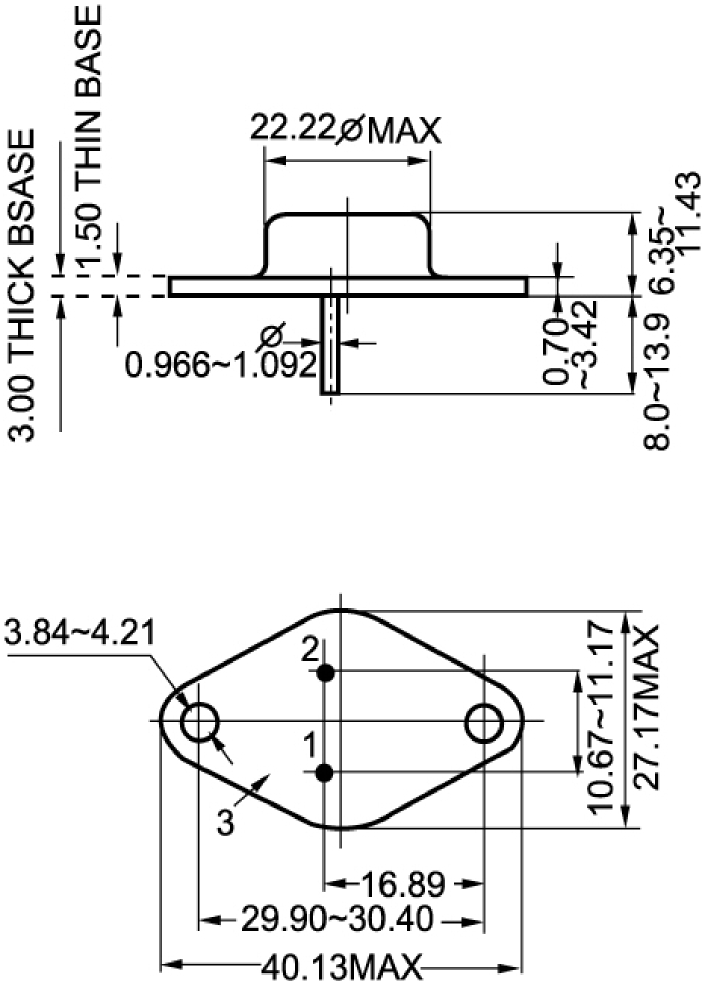

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)